E. Lattice Semiconductor Corporation - <u>LFE3-150EA-6FN1156I Datasheet</u>



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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	18625
Number of Logic Elements/Cells	149000
Total RAM Bits	7014400
Number of I/O	586
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA
Supplier Device Package	1156-FPBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-150ea-6fn1156i

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Introduction

The LatticeECP3[™] (EConomy Plus Third generation) family of FPGA devices is optimized to deliver high performance features such as an enhanced DSP architecture, high speed SERDES and high speed source synchronous interfaces in an economical FPGA fabric. This combination is achieved through advances in device architecture and the use of 65 nm technology making the devices suitable for high-volume, high-speed, low-cost applications.

The LatticeECP3 device family expands look-up-table (LUT) capacity to 149K logic elements and supports up to 586 user I/Os. The LatticeECP3 device family also offers up to 320 18 x 18 multipliers and a wide range of parallel I/O standards.

The LatticeECP3 FPGA fabric is optimized with high performance and low cost in mind. The LatticeECP3 devices utilize reconfigurable SRAM logic technology and provide popular building blocks such as LUT-based logic, distributed and embedded memory, Phase Locked Loops (PLLs), Delay Locked Loops (DLLs), pre-engineered source synchronous I/O support, enhanced sysDSP slices and advanced configuration support, including encryption and dual-boot capabilities.

The pre-engineered source synchronous logic implemented in the LatticeECP3 device family supports a broad range of interface standards, including DDR3, XGMII and 7:1 LVDS.

The LatticeECP3 device family also features high speed SERDES with dedicated PCS functions. High jitter tolerance and low transmit jitter allow the SERDES plus PCS blocks to be configured to support an array of popular data protocols including PCI Express, SMPTE, Ethernet (XAUI, GbE, and SGMII) and CPRI. Transmit Pre-emphasis and Receive Equalization settings make the SERDES suitable for transmission and reception over various forms of media.

The LatticeECP3 devices also provide flexible, reliable and secure configuration options, such as dual-boot capability, bit-stream encryption, and TransFR field upgrade features.

The Lattice Diamond[™] and ispLEVER[®] design software allows large complex designs to be efficiently implemented using the LatticeECP3 FPGA family. Synthesis library support for LatticeECP3 is available for popular logic synthesis tools. Diamond and ispLEVER tools use the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the LatticeECP3 device. The tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) modules for the LatticeECP3 family. By using these configurable soft core IPs as standardized blocks, designers are free to concentrate on the unique aspects of their design, increasing their productivity.



LatticeECP3 Family Data Sheet Architecture

June 2013

Data Sheet DS1021

Architecture Overview

Each LatticeECP3 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM[™] Embedded Block RAM (EBR) and rows of sys-DSP[™] Digital Signal Processing slices, as shown in Figure 2-1. The LatticeECP3-150 has four rows of DSP slices; all other LatticeECP3 devices have two rows of DSP slices. In addition, the LatticeECP3 family contains SERDES Quads on the bottom of the device.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and Programmable Functional Unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

The LatticeECP3 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18Kbit fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, LatticeECP3 devices contain up to two rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The LatticeECP3 devices feature up to 16 embedded 3.2 Gbps SERDES (Serializer / Deserializer) channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of four SERDES channels, along with its Physical Coding Sub-layer (PCS) block, creates a quad. The functionality of the SERDES/PCS quads can be controlled by memory cells set during device configuration or by registers that are addressable during device operation. The registers in every quad can be programmed via the SERDES Client Interface (SCI). These quads (up to four) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysl/O buffers. The sysl/O buffers of the LatticeECP3 devices are arranged in seven banks, allowing the implementation of a wide variety of I/O standards. In addition, a separate I/O bank is provided for the programming interfaces. 50% of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3.

The LatticeECP3 registers in PFU and sysl/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The LatticeECP3 architecture provides two Delay Locked Loops (DLLs) and up to ten Phase Locked Loops (PLLs). The PLL and DLL blocks are located at the end of the EBR/DSP rows.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located toward the center of this EBR row. Every device in the LatticeECP3 family supports a sysCONFIG[™] port located in the corner between banks one and two, which allows for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The LatticeECP3 devices use 1.2 V as their core voltage.

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Figure 2-10. Primary Clock Sources for LatticeECP3-35



Note: Clock inputs can be configured in differential or single-ended mode.

Figure 2-11. Primary Clock Sources for LatticeECP3-70, -95, -150



Note: Clock inputs can be configured in differential or single-ended mode.



Figure 2-20. Sources of Edge Clock (Left and Right Edges)



Figure 2-21. Sources of Edge Clock (Top Edge)



The edge clocks have low injection delay and low skew. They are used to clock the I/O registers and thus are ideal for creating I/O interfaces with a single clock signal and a wide data bus. They are also used for DDR Memory or Generic DDR interfaces.



This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-23 compares the fully serial implementation to the mixed parallel and serial implementation.



Figure 2-23. Comparison of General DSP and LatticeECP3 Approaches

LatticeECP3 sysDSP Slice Architecture Features

The LatticeECP3 sysDSP Slice has been significantly enhanced to provide functions needed for advanced processing applications. These enhancements provide improved flexibility and resource utilization.

The LatticeECP3 sysDSP Slice supports many functions that include the following:

- Multiply (one 18 x 36, two 18 x 18 or four 9 x 9 Multiplies per Slice)
- Multiply (36 x 36 by cascading across two sysDSP slices)
- Multiply Accumulate (up to 18 x 36 Multipliers feeding an Accumulator that can have up to 54-bit resolution)
- Two Multiplies feeding one Accumulate per cycle for increased processing with lower latency (two 18 x 18 Multiplies feed into an accumulator that can accumulate up to 52 bits)
- Flexible saturation and rounding options to satisfy a diverse set of applications situations
- Flexible cascading across DSP slices
 - Minimizes fabric use for common DSP and ALU functions
 - Enables implementation of FIR Filter or similar structures using dedicated sysDSP slice resources only
 - Provides matching pipeline registers
 - Can be configured to continue cascading from one row of sysDSP slices to another for longer cascade chains
- Flexible and Powerful Arithmetic Logic Unit (ALU) Supports:
 - Dynamically selectable ALU OPCODE
 - Ternary arithmetic (addition/subtraction of three inputs)
 - Bit-wise two-input logic operations (AND, OR, NAND, NOR, XOR and XNOR)
 - Eight flexible and programmable ALU flags that can be used for multiple pattern detection scenarios, such



Figure 2-31. MULTADDSUBSUM Slice 1



Advanced sysDSP Slice Features

Cascading

The LatticeECP3 sysDSP slice has been enhanced to allow cascading. Adder trees are implemented fully in sys-DSP slices, improving the performance. Cascading of slices uses the signals CIN, COUT and C Mux of the slice.

Addition

The LatticeECP3 sysDSP slice allows for the bypassing of multipliers and cascading of adder logic. High performance adder functions are implemented without the use of LUTs. The maximum width adders that can be implemented are 54-bit.

Rounding

The rounding operation is implemented in the ALU and is done by adding a constant followed by a truncation operation. The rounding methods supported are:

- Rounding to zero (RTZ)
- Rounding to infinity (RTI)
- Dynamic rounding
- Random rounding
- Convergent rounding



On-Chip Programmable Termination

The LatticeECP3 supports a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 40, 50, or 60 Ohms. External termination to Vtt should be used for DDR2 and DDR3 memory controller implementation.
- Common mode termination of 80, 100, 120 Ohms for differential inputs

Figure 2-39. On-Chip Termination



Programmable resistance (40, 50 and 60 Ohms)
Parallel Single-Ended Input

Differential Input

See Table 2-12 for termination options for input modes.

Table 2-12. On-Chip Termination Options for Input Modes

IO_TYPE	TERMINATE to VTT ^{1, 2}	DIFFERENTIAL TERMINATION RESISTOR ¹
LVDS25	þ	80, 100, 120
BLVDS25	þ	80, 100, 120
MLVDS	þ	80, 100, 120
HSTL18_I	40, 50, 60	þ
HSTL18_II	40, 50, 60	þ
HSTL18D_I	40, 50, 60	þ
HSTL18D_II	40, 50, 60	þ
HSTL15_I	40, 50, 60	þ
HSTL15D_I	40, 50, 60	þ
SSTL25_I	40, 50, 60	þ
SSTL25_II	40, 50, 60	þ
SSTL25D_I	40, 50, 60	þ
SSTL25D_II	40, 50, 60	þ
SSTL18_I	40, 50, 60	þ
SSTL18_II	40, 50, 60	þ
SSTL18D_I	40, 50, 60	þ
SSTL18D_II	40, 50, 60	þ
SSTL15	40, 50, 60	þ
SSTL15D	40, 50, 60	þ

1. TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature. Use of TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in

an I/O bank.

On-chip termination tolerance +/- 20%

2. External termination to VTT should be used when implementing DDR2 and DDR3 memory controller.



Package	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
256 ftBGA	1	1	—	—	—
328 csBGA	2 channels	—	—	—	—
484 fpBGA	1	1	1	1	
672 fpBGA	—	1	2	2	2
1156 fpBGA	—	—	3	3	4

SERDES Block

A SERDES receiver channel may receive the serial differential data stream, equalize the signal, perform Clock and Data Recovery (CDR) and de-serialize the data stream before passing the 8- or 10-bit data to the PCS logic. The SERDES transmitter channel may receive the parallel 8- or 10-bit data, serialize the data and transmit the serial bit stream through the differential drivers. Figure 2-41 shows a single-channel SERDES/PCS block. Each SERDES channel provides a recovered clock and a SERDES transmit clock to the PCS block and to the FPGA core logic.

Each transmit channel, receiver channel, and SERDES PLL shares the same power supply (VCCA). The output and input buffers of each channel have their own independent power supplies (VCCOB and VCCIB).

Figure 2-41. Simplified Channel Block Diagram for SERDES/PCS Block



PCS

As shown in Figure 2-41, the PCS receives the parallel digital data from the deserializer and selects the polarity, performs word alignment, decodes (8b/10b), provides Clock Tolerance Compensation and transfers the clock domain from the recovered clock to the FPGA clock via the Down Sample FIFO.

For the transmit channel, the PCS block receives the parallel data from the FPGA core, encodes it with 8b/10b, selects the polarity and passes the 8/10 bit data to the transmit SERDES channel.

The PCS also provides bypass modes that allow a direct 8-bit or 10-bit interface from the SERDES to the FPGA logic. The PCS interface to the FPGA can also be programmed to run at 1/2 speed for a 16-bit or 20-bit interface to the FPGA logic.



Enhanced Configuration Options

LatticeECP3 devices have enhanced configuration features such as: decryption support, TransFR™ I/O and dualboot image support.

1. TransFR (Transparent Field Reconfiguration)

TransFR I/O (TFR) is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a single ispVM command. TransFR I/O allows I/O states to be frozen during device configuration. This allows the device to be field updated with a minimum of system disruption and downtime. See TN1087, Minimizing System Interruption During Configuration Using TransFR Technology for details.

2. Dual-Boot Image Support

Dual-boot images are supported for applications requiring reliable remote updates of configuration data for the system FPGA. After the system is running with a basic configuration, a new boot image can be downloaded remotely and stored in a separate location in the configuration storage device. Any time after the update the LatticeECP3 can be re-booted from this new configuration file. If there is a problem, such as corrupt data during download or incorrect version number with this new boot image, the LatticeECP3 device can revert back to the original backup golden configuration and try again. This all can be done without power cycling the system. For more information, please see TN1169, LatticeECP3 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeECP3 devices have dedicated logic to perform Cycle Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, the LatticeECP3 device can also be programmed to utilize a Soft Error Detect (SED) mode that checks for soft errors in configuration SRAM. The SED operation can be run in the background during user mode. If a soft error occurs, during user mode (normal operation) the device can be programmed to generate an error signal.

For further information on SED support, please see TN1184, LatticeECP3 Soft Error Detection (SED) Usage Guide.

External Resistor

LatticeECP3 devices require a single external, 10 kOhm \pm 1% value between the XRES pin and ground. Device configuration will not be completed if this resistor is missing. There is no boundary scan register on the external resistor pad.

On-Chip Oscillator

Every LatticeECP3 device has an internal CMOS oscillator which is used to derive a Master Clock (MCCLK) for configuration. The oscillator and the MCCLK run continuously and are available to user logic after configuration is completed. The software default value of the MCCLK is nominally 2.5 MHz. Table 2-16 lists all the available MCCLK frequencies. When a different Master Clock is selected during the design process, the following sequence takes place:

- 1. Device powers up with a nominal Master Clock frequency of 3.1 MHz.
- 2. During configuration, users select a different master clock frequency.
- 3. The Master Clock frequency changes to the selected frequency once the clock configuration bits are received.
- 4. If the user does not select a master clock frequency, then the configuration bitstream defaults to the MCCLK frequency of 2.5 MHz.

This internal 130 MHz +/- 15% CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1169, LatticeECP3 sysCONFIG Usage Guide.



SERDES Power Supply Requirements^{1, 2, 3}

Symbol	Description	Тур.	Max.	Units
Standby (Power Do	own)	•		1
I _{CCA-SB}	V _{CCA} current (per channel)	3	5	mA
I _{CCIB-SB}	Input buffer current (per channel)		—	mA
I _{CCOB-SB}	Output buffer current (per channel)	—	_	mA
Operating (Data Ra	ite = 3.2 Gbps)			•
I _{CCA-OP}	V _{CCA} current (per channel)	68	77	mA
I _{CCIB-OP}	Input buffer current (per channel)	7	mA	
I _{CCOB-OP}	Output buffer current (per channel)	19	25	mA
Operating (Data Ra	ite = 2.5 Gbps)	·		·
I _{CCA-OP}	V _{CCA} current (per channel)	66	76	mA
I _{CCIB-OP}	Input buffer current (per channel)	4	5	mA
I _{CCOB-OP}	Output buffer current (per channel)	15	18	mA
Operating (Data Ra	ite = 1.25 Gbps)			·
I _{CCA-OP}	V _{CCA} current (per channel)	62	72	mA
I _{CCIB-OP}	Input buffer current (per channel)	4	5	mA
I _{CCOB-OP}	Output buffer current (per channel)	18	mA	
Operating (Data Ra	ite = 250 Mbps)	·		·
I _{CCA-OP}	V _{CCA} current (per channel)	55	65	mA
I _{CCIB-OP}	Input buffer current (per channel)	4	5	mA
I _{CCOB-OP}	Output buffer current (per channel)	14	17	mA
Operating (Data Ra	ite = 150 Mbps)	·		·
I _{CCA-OP}	V _{CCA} current (per channel)	55	65	mA
I _{CCIB-OP}	Input buffer current (per channel)	4	5	mA
I _{CCOB-OP}	Output buffer current (per channel)	14	17	mA

1. Equalization enabled, pre-emphasis disabled.

2. One quarter of the total quad power (includes contribution from common circuits, all channels in the quad operating, pre-emphasis disabled, equalization enabled).

3. Pre-emphasis adds 20 mA to ICCA-OP data.



Units V

Ω

Ω

Ω

Ω

٧

٧

V

V

mΑ

BLVDS25

The LatticeECP3 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.





Table 3-2. BLVDS25 DC Conditions¹

V_{CCIO}

ZOUT

R_S

R_{TL}

 R_{TR} V_{OH}

VOL

VOD

V_{CM}

	-	-		
		Тур	ical	
Parameter	Description	Ζο = 45 Ω	Ζο = 90 Ω	
CCIO	Output Driver Supply (+/– 5%)	2.50	2.50	

10.00

90.00

45.00

45.00

1.38

1.12

0.25

1.25

11.24

10.00

90.00

90.00

90.00

1.48

1.02

0.46

1.25

10.20

Over Recommended Operating Conditions

 I_{DC} 1. For input buffer, see LVDS table.

Driver Impedance

Output High Voltage

Output Low Voltage

DC Output Current

Output Differential Voltage

Output Common Mode Voltage

Driver Series Resistor (+/- 1%)

Driver Parallel Resistor (+/- 1%)

Receiver Termination (+/- 1%)



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			-	-8	-7		-6		
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
Generic DDRX2 In	puts with Clock and Data (>10bits	s wide) are Aligned at I	Pin (GDD	RX2_RX	.ECLK.A	ligned)	1		
(No CLKDIV)									
Left and Right Side	es Using DLLCLKPIN for Clock Ir			0.005	1	0.005	1	0.005	
^t DVACLKGDDR	Data Setup Before CLK	ECP3-150EA		0.225		0.225		0.225	
	Data Hold After CLK	ECP3-150EA	0.775	-	0.775		0.775		
^T MAX_GDDR	DDRX2 Clock Frequency	ECP3-150EA	_	460	_	385	_	345	MHZ
^t DVACLKGDDR	Data Setup Before CLK	ECP3-70EA/95EA		0.225		0.225		0.225	UI
^t DVECLKGDDR	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775		0.775	—	UI
fMAX_GDDR	DDRX2 Clock Frequency	ECP3-70EA/95EA		460		385		311	MHZ
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-35EA	_	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790		0.790	—	0.790	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	_	460	_	385	_	311	MHz
t _{DVACLKGDDR}	Data Setup Before CLK (Left and Right Sides)	ECP3-17EA	_	0.210	_	0.210		0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA		460		385		311	MHz
Top Side Using PC	LK Pin for Clock Input								
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-150EA		0.225		0.225		0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	_	235	—	170		130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	_	0.225	_	0.225	_	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	_	235		170	—	130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-35EA	_	0.210		0.210		0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA		235		170		130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-17EA		0.210		0.210		0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	—	0.790		0.790		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	_	235		170		130	MHz
Generic DDRX2 In Input	puts with Clock and Data (<10 Bit	ts Wide) Centered at P	in (GDDF	RX2_RX.I	DQS.Cen	tered) U	sing DQ	S Pin for	Clock
Left and Right Side	es								
t _{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	330	_	330		352		ps
t _{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	330	—	330	—	352	_	ps
f _{MAX GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	400	_	400	_	375	MHz
Generic DDRX2 In	puts with Clock and Data (<10 Bit	ts Wide) Aligned at Pin	(GDDR)	(2_RX.D0	QS.Align	ed) Using	g DQS Pi	n for Clo	ck Input
Left and Right Side	es								
t _{DVACLKGDDR}	Data Setup Before CLK	All ECP3EA Devices	_	0.225	_	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	_	0.775	_	UI
f _{MAX GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	400	_	400	—	375	MHz
Generic DDRX1 O	utput with Clock and Data (>10 B	its Wide) Centered at P	in (GDD	RX1_TX.	SCLK.Ce	ntered)10)		
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670	—	670		670		ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f _{MAX} GDDR	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
	Data Valid Before CLK	ECP3-70EA/95EA	666	—	665		664	—	ps
	Data Valid After CLK	ECP3-70EA/95EA	666		665		664		ps
BIAGDDIT	1	1		I		l			· ·

Over Recommended Commercial Operating Conditions



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

						6			
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
fMAX GDDB	DDRX1 Clock Frequency	ECP3-70EA/95EA		250		250	_	250	MHz
	Data Valid Before CLK	ECP3-35EA	683	—	688	_	690	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	683	_	688	_	690	_	ps
f _{MAX GDDR}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250	_	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	683	—	688	_	690	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	—	ps
f _{MAX} GDDR	DDRX1 Clock Frequency	ECP3-17EA	_	250	_	250	—	250	MHz
Generic DDRX1 Ou	itput with Clock and Data Aligned	at Pin (GDDRX1_TX.	SCLK.Ali	gned) ¹⁰					
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-150EA		335	_	338	—	341	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA		250	_	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-70EA/95EA	_	339	_	343	—	347	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-70EA/95EA	_	339	_	343	_	347	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250	_	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-35EA	_	322	_	320	_	321	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-35EA	_	322	_	320	_	321	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250	_	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-17EA	_	322	_	320	_	321	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-17EA	_	322	_	320	—	321	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA		250	_	250	—	250	MHz
Generic DDRX1 Ou	itput with Clock and Data (<10 Bi	ts Wide) Centered at P	in (GDD	RX1_TX.	DQS.Cen	tered) ¹⁰			
Left and Right Side	es								
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670	_	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	_	250		250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-70EA/95EA	657	—	652	_	650	_	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-35EA	670	—	675	—	676	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	670	—	675	_	676	_	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	_	250	_	250	—	250	MHz
Generic DDRX2 Ou	itput with Clock and Data (>10 Bi	ts Wide) Aligned at Pir	n (GDDR	X2_TX.A	igned)				
Left and Right Side	es								
t _{DIBGDDR}	Data Invalid Before Clock	All ECP3EA Devices		200		210		220	ps
t _{DIAGDDR}	Data Invalid After Clock	All ECP3EA Devices	_	200	_	210	_	220	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	500	_	420	—	375	MHz
Generic DDRX2 Ou	Itput with Clock and Data (>10 Bi	ts Wide) Centered at P	in Using		L (GDDF	X2_TX.D	QSDLL.	Centered)11
Left and Right Side	es								
t _{DVBGDDR}	Data Valid Before CLK	All ECP3EA Devices	400		400		431		ps
t _{DVAGDDR}	Data Valid After CLK	All ECP3EA Devices	400		400	—	432	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	400	_	400	—	375	MHz

Over Recommended Commercial Operating Conditions



LatticeECP3 Family Timing Adders^{1, 2, 3, 4, 5, 7} (Continued)

Over Recommended Commercial	Operating	Conditions
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Buffer Type	Description	-8	-7	-6	Units
LVCMOS15_4mA	LVCMOS 1.5 4 mA drive, fast slew rate	0.21	0.25	0.29	ns
LVCMOS15_8mA	LVCMOS 1.5 8 mA drive, fast slew rate	0.05	0.07	0.09	ns
LVCMOS12_2mA	LVCMOS 1.2 2 mA drive, fast slew rate	0.43	0.51	0.59	ns
LVCMOS12_6mA	LVCMOS 1.2 6 mA drive, fast slew rate	0.23	0.28	0.33	ns
LVCMOS33_4mA	LVCMOS 3.3 4 mA drive, slow slew rate	1.44	1.58	1.72	ns
LVCMOS33_8mA	LVCMOS 3.3 8 mA drive, slow slew rate	0.98	1.10	1.22	ns
LVCMOS33_12mA	LVCMOS 3.3 12 mA drive, slow slew rate	0.67	0.77	0.86	ns
LVCMOS33_16mA	LVCMOS 3.3 16 mA drive, slow slew rate	0.97	1.09	1.21	ns
LVCMOS33_20mA	LVCMOS 3.3 20 mA drive, slow slew rate	0.67	0.76	0.85	ns
LVCMOS25_4mA	LVCMOS 2.5 4 mA drive, slow slew rate	1.48	1.63	1.78	ns
LVCMOS25_8mA	LVCMOS 2.5 8 mA drive, slow slew rate	1.02	1.14	1.27	ns
LVCMOS25_12mA	LVCMOS 2.5 12 mA drive, slow slew rate	0.74	0.84	0.94	ns
LVCMOS25_16mA	LVCMOS 2.5 16 mA drive, slow slew rate	1.02	1.14	1.26	ns
LVCMOS25_20mA	LVCMOS 2.5 20 mA drive, slow slew rate	0.74	0.83	0.93	ns
LVCMOS18_4mA	LVCMOS 1.8 4 mA drive, slow slew rate	1.60	1.77	1.93	ns
LVCMOS18_8mA	LVCMOS 1.8 8 mA drive, slow slew rate	1.11	1.25	1.38	ns
LVCMOS18_12mA	LVCMOS 1.8 12 mA drive, slow slew rate	0.87	0.98	1.09	ns
LVCMOS18_16mA	LVCMOS 1.8 16 mA drive, slow slew rate	0.86	0.97	1.07	ns
LVCMOS15_4mA	LVCMOS 1.5 4 mA drive, slow slew rate	1.71	1.89	2.08	ns
LVCMOS15_8mA	LVCMOS 1.5 8 mA drive, slow slew rate	1.20	1.34	1.48	ns
LVCMOS12_2mA	LVCMOS 1.2 2 mA drive, slow slew rate	1.37	1.56	1.74	ns
LVCMOS12_6mA	LVCMOS 1.2 6 mA drive, slow slew rate	1.11	1.27	1.43	ns
PCI33	PCI, VCCIO = 3.3 V	-0.12	-0.13	-0.14	ns

1. Timing adders are characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Not all I/O standards and drive strengths are supported for all banks. See the Architecture section of this data sheet for details.

5. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

6. This data does not apply to the LatticeECP3-17EA device.

7. For details on -9 speed grade devices, please contact your Lattice Sales Representative.



Figure 3-14. Jitter Transfer – 3.125 Gbps



Figure 3-15. Jitter Transfer – 2.5 Gbps





Figure 3-19. Test Loads

Test Loads









LatticeECP3 Family Data Sheet Ordering Information

April 2014

Data Sheet DS1021

LatticeECP3 Part Number Description



1. Green = Halogen free and lead free.

Ordering Information

LatticeECP3 devices have top-side markings, for commercial and industrial grades, as shown below:



Note: See PCN 05A-12 for information regarding a change to the top-side mark logo.

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LatticeECP3 Devices, Green and Lead-Free Packaging

The following devices may have associated errata. Specific devices with associated errata will be notated with a footnote.

Part Number	Voltage	Grade	Power	Package ¹	Pins	Temp.	LUTs (K)
LFE3-17EA-6FTN256C	1.2 V	-6	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-7FTN256C	1.2 V	-7	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-8FTN256C	1.2 V	-8	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-6LFTN256C	1.2 V	-6	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-7LFTN256C	1.2 V	-7	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-8LFTN256C	1.2 V	-8	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-6MG328C	1.2 V	-6	STD	Green csBGA	328	COM	17
LFE3-17EA-7MG328C	1.2 V	-7	STD	Green csBGA	328	COM	17
LFE3-17EA-8MG328C	1.2 V	-8	STD	Green csBGA	328	COM	17
LFE3-17EA-6LMG328C	1.2 V	-6	LOW	Green csBGA	328	COM	17
LFE3-17EA-7LMG328C	1.2 V	-7	LOW	Green csBGA	328	COM	17
LFE3-17EA-8LMG328C	1.2 V	-8	LOW	Green csBGA	328	COM	17
LFE3-17EA-6FN484C	1.2 V	-6	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-7FN484C	1.2 V	-7	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-8FN484C	1.2 V	-8	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-6LFN484C	1.2 V	-6	LOW	Lead-Free fpBGA	484	COM	17
LFE3-17EA-7LFN484C	1.2 V	-7	LOW	Lead-Free fpBGA	484	COM	17
LFE3-17EA-8LFN484C	1.2 V	-8	LOW	Lead-Free fpBGA	484	COM	17

Commercial

1. Green = Halogen free and lead free.

Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-35EA-6FTN256C	1.2 V	-6	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-7FTN256C	1.2 V	-7	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-8FTN256C	1.2 V	-8	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-6LFTN256C	1.2 V	-6	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-7LFTN256C	1.2 V	-7	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-8LFTN256C	1.2 V	-8	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-6FN484C	1.2 V	-6	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-7FN484C	1.2 V	-7	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-8FN484C	1.2 V	-8	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-6LFN484C	1.2 V	-6	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-7LFN484C	1.2 V	-7	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-8LFN484C	1.2 V	-8	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	33
LFE3-35EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	33
LFE3-35EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	33

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.



Industrial

The following devices may have associated errata. Specific devices with associated errata will be notated with a footnote.

Part Number	Voltage	Grade	Power	Package ¹	Pins	Temp.	LUTs (K)
LFE3-17EA-6FTN256I	1.2 V	-6	STD	Lead-Free ftBGA	256	IND	17
LFE3-17EA-7FTN256I	1.2 V	-7	STD	Lead-Free ftBGA	256	IND	17
LFE3-17EA-8FTN256I	1.2 V	-8	STD	Lead-Free ftBGA	256	IND	17
LFE3-17EA-6LFTN256I	1.2 V	-6	LOW	Lead-Free ftBGA	256	IND	17
LFE3-17EA-7LFTN256I	1.2 V	-7	LOW	Lead-Free ftBGA	256	IND	17
LFE3-17EA-8LFTN256I	1.2 V	-8	LOW	Lead-Free ftBGA	256	IND	17
LFE3-17EA-6MG328I	1.2 V	-6	STD	Lead-Free csBGA	328	IND	17
LFE3-17EA-7MG328I	1.2 V	-7	STD	Lead-Free csBGA	328	IND	17
LFE3-17EA-8MG328I	1.2 V	-8	STD	Lead-Free csBGA	328	IND	17
LFE3-17EA-6LMG328I	1.2 V	-6	LOW	Green csBGA	328	IND	17
LFE3-17EA-7LMG328I	1.2 V	-7	LOW	Green csBGA	328	IND	17
LFE3-17EA-8LMG328I	1.2 V	-8	LOW	Green csBGA	328	IND	17
LFE3-17EA-6FN484I	1.2 V	-6	STD	Lead-Free fpBGA	484	IND	17
LFE3-17EA-7FN484I	1.2 V	-7	STD	Lead-Free fpBGA	484	IND	17
LFE3-17EA-8FN484I	1.2 V	-8	STD	Lead-Free fpBGA	484	IND	17
LFE3-17EA-6LFN484I	1.2 V	-6	LOW	Lead-Free fpBGA	484	IND	17
LFE3-17EA-7LFN484I	1.2 V	-7	LOW	Lead-Free fpBGA	484	IND	17
LFE3-17EA-8LFN484I	1.2 V	-8	LOW	Lead-Free fpBGA	484	IND	17

1. Green = Halogen free and lead free.

Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-35EA-6FTN256I	1.2 V	-6	STD	Lead-Free ftBGA	256	IND	33
LFE3-35EA-7FTN256I	1.2 V	-7	STD	Lead-Free ftBGA	256	IND	33
LFE3-35EA-8FTN256I	1.2 V	-8	STD	Lead-Free ftBGA	256	IND	33
LFE3-35EA-6LFTN256I	1.2 V	-6	LOW	Lead-Free ftBGA	256	IND	33
LFE3-35EA-7LFTN256I	1.2 V	-7	LOW	Lead-Free ftBGA	256	IND	33
LFE3-35EA-8LFTN256I	1.2 V	-8	LOW	Lead-Free ftBGA	256	IND	33
LFE3-35EA-6FN484I	1.2 V	-6	STD	Lead-Free fpBGA	484	IND	33
LFE3-35EA-7FN484I	1.2 V	-7	STD	Lead-Free fpBGA	484	IND	33
LFE3-35EA-8FN484I	1.2 V	-8	STD	Lead-Free fpBGA	484	IND	33
LFE3-35EA-6LFN484I	1.2 V	-6	LOW	Lead-Free fpBGA	484	IND	33
LFE3-35EA-7LFN484I	1.2 V	-7	LOW	Lead-Free fpBGA	484	IND	33
LFE3-35EA-8LFN484I	1.2 V	-8	LOW	Lead-Free fpBGA	484	IND	33
LFE3-35EA-6FN672I	1.2 V	-6	STD	Lead-Free fpBGA	672	IND	33
LFE3-35EA-7FN672I	1.2 V	-7	STD	Lead-Free fpBGA	672	IND	33
LFE3-35EA-8FN672I	1.2 V	-8	STD	Lead-Free fpBGA	672	IND	33
LFE3-35EA-6LFN672I	1.2 V	-6	LOW	Lead-Free fpBGA	672	IND	33
LFE3-35EA-7LFN672I	1.2 V	-7	LOW	Lead-Free fpBGA	672	IND	33
LFE3-35EA-8LFN672I	1.2 V	-8	LOW	Lead-Free fpBGA	672	IND	33

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.



LatticeECP3 Family Data Sheet Revision History

March 2015

Data Sheet DS1021

Date	Version	Section	Change Summary		
March 2015 2.8EA		Pinout Information All	Updated Package Pinout Information section. Changed reference to http://www.latticesemi.com/Products/FPGAandCPLD/LatticeECP3.		
			Minor style/formatting changes.		
April 2014 02.7EA		DC and Switching	Updated LatticeECP3 Supply Current (Standby) table power numbers.		
		Characteristics	Removed speed grade -9 timing numbers in the following sections: — Typical Building Block Function Performance — LatticeECP3 External Switching Characteristics — LatticeECP3 Internal Switching Characteristics — LatticeECP3 Family Timing Adders		
		Ordering Information	Removed ordering information for -9 speed grade devices.		
March 2014	02.6EA	DC and Switching Characteristics	Added information to the sysl/O Single-Ended DC Electrical Character- istics section footnote.		
February 2014 02.5EA	02.5EA	DC and Switching Characteristics	Updated Hot Socketing Specifications table. Changed I_{Pw} to I_{PD} in footnote 3.		
			Updated the following figures: — Figure 3-25, sysCONFIG Port Timing — Figure 3-27, Wake-Up Timing		
		Supplemental Information	Added technical note references.		
September 2013 02.4EA	02.4EA	DC and Switching Characteristics	Updated the Wake-Up Timing Diagram		
			Added the following figures: — Master SPI POR Waveforms — SPI Configuration Waveforms — Slave SPI HOLDN Waveforms		
		Added tIODISS and tIOENSS parameters in LatticeECP3 sysCONFIG Port Timing Specifications table.			
June 2013 02.3EA	Architecture	sysl/O Buffer Banks text section – Updated description of "Top (Bank 0 and Bank 1) and Bottom syslO Buffer Pairs (Single-Ended Outputs Only)" for hot socketing information.			
			sysl/O Buffer Banks text section – Updated description of "Configuration Bank sysl/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)" for PCI clamp information.		
			On-Chip Oscillator section – clarified the speed of the internal CMOS oscillator (130 MHz +/- 15%).		
	-		Architecture Overview section – Added information on the state of the register on power up and after configuration.		
		DC and Switching Characteristics	sysl/O Recommended Operating Conditions table – Removed reference to footnote 1 from RSDS standard.		
			sysl/O Single-Ended DC Electrical Characteristics table – Modified foot- note 1.		
			Added Oscillator Output Frequency table.		
			LatticeECP3 sysCONFIG Port Timing Specifications table – Updated min. column for t _{CODO} parameter.		
			LatticeECP3 Family Timing Adders table – Description column, references to VCCIO = 3.0V changed to 3.3V. For PPLVDS, description changed from emulated to True LVDS and VCCIO = 2.5V changed to VCCIO = 2.5V or 3.3V.		

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